

## B5819W SCHOTTKY BARRIER DIODE

### FEATURES

Power dissipation

$P_D$ : 450 mW ( $T_{amb}=25^\circ\text{C}$ )

Collector current

$I_F$ : 1 A

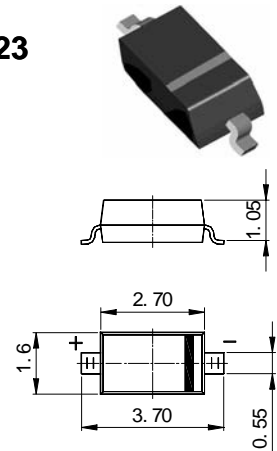
Collector-base voltage

$V_R$ : 40 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$

### SOD-123



Unit: mm

**MARKING: SL**

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 1\text{mA}$	40		V
Reverse voltage leakage current	$I_R$	$V_R=40\text{V}$ $V_R=4\text{V}$ $V_R=6\text{V}$		1 0.05 0.075	mA
Forward voltage	$V_F$	$I_F=0.1\text{A}$ $I_F=1\text{A}$ $I_F=3\text{A}$		0.45 0.6 0.9	V
Diode capacitance	$C_D$	$V_R=4\text{V}, f=1\text{MHz}$		120	pF